

### 2SA1235A TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 0.2 \text{ W (Tamb=25°C)}$$

Collector current

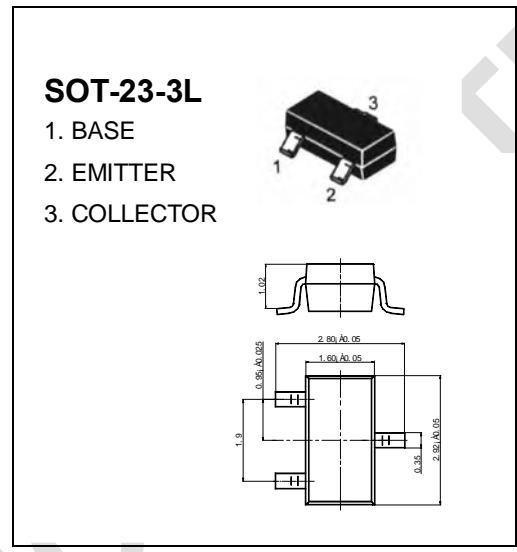
$$I_{CM} : -0.2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1 \text{ mA}, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-6		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -60 \text{ V}, I_E = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -6 \text{ V}, I_C = -1 \text{ mA}$	150	500	
	$h_{FE(2)}$	$V_{CE} = -6 \text{ V}, I_C = -0.1 \text{ mA}$	90		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-0.3	V
Base-emitter voltage	$V_{BE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-1	V
Transition frequency	$f_T$	$V_{CE} = -6 \text{ V}, I_C = -10 \text{ mA}$	180		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Marking	M·E	M·F
Range	150-300	250-500